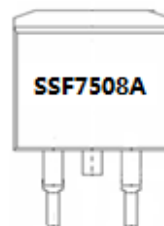


Main Product Characteristics:

| | |
|--------------|--------------------|
| V_{DSS} | 75V |
| $R_{DS(on)}$ | 6m Ω (typ.) |
| I_D | 100A |


D2PAK

**Marking and pin
Assignment**

Schematic diagram
Features and Benefits:

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 175°C operating temperature


Description:

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute max Rating:

| Symbol | Parameter | Max. | Units |
|--------------------------|--|--------------|-------|
| $I_D @ TC = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ ① | 100 | A |
| $I_D @ TC = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ ① | 70 | |
| I_{DM} | Pulsed Drain Current ② | 400 | |
| $P_D @ TC = 25^\circ C$ | Power Dissipation ③ | 200 | W |
| | Linear Derating Factor | 1.3 | W/°C |
| V_{DS} | Drain-Source Voltage | 75 | V |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| E_{AS} | Single Pulse Avalanche Energy @ $L=0.3mH$ ② | 205 | mJ |
| I_{AS} | Avalanche Current @ $L=0.3mH$ ② | 37 | A |
| T_J T_{STG} | Operating Junction and Storage Temperature Range | -55 to + 175 | °C |

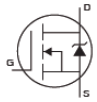
Thermal Resistance

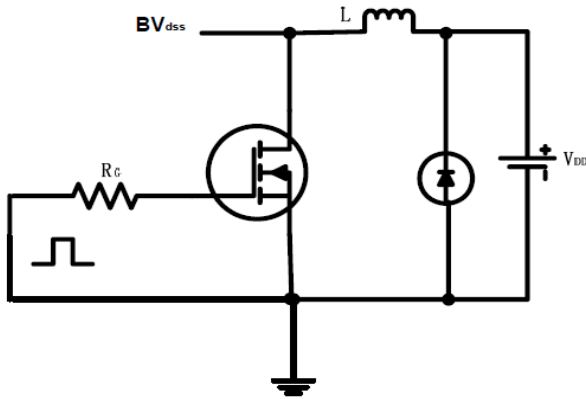
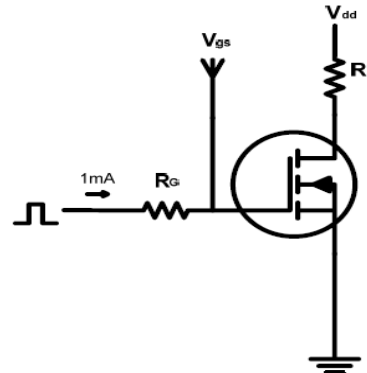
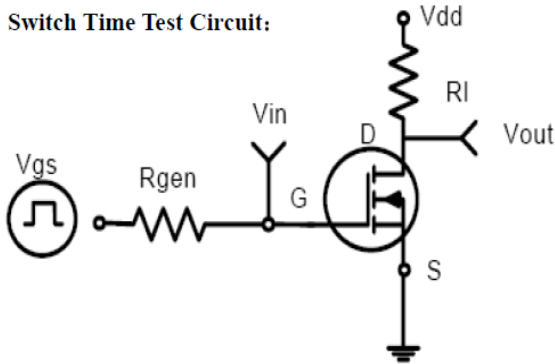
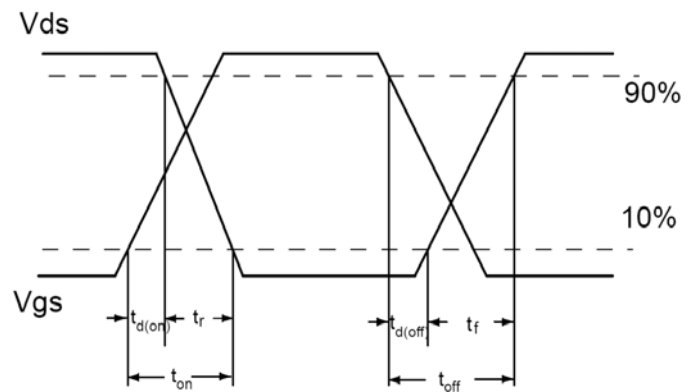
| Symbol | Characterizes | Typ. | Max. | Units |
|-----------------|--|------|------|-------|
| $R_{\theta JC}$ | Junction-to-case ^③ | — | 0.75 | °C/W |
| $R_{\theta JA}$ | Junction-to-ambient (t ≤ 10s) ^④ | — | 62 | °C/W |
| | Junction-to-Ambient (PCB mounted, steady-state) ^④ | — | 40 | °C/W |

Electrical Characterizes @ $T_A=25^\circ\text{C}$ unless otherwise specified

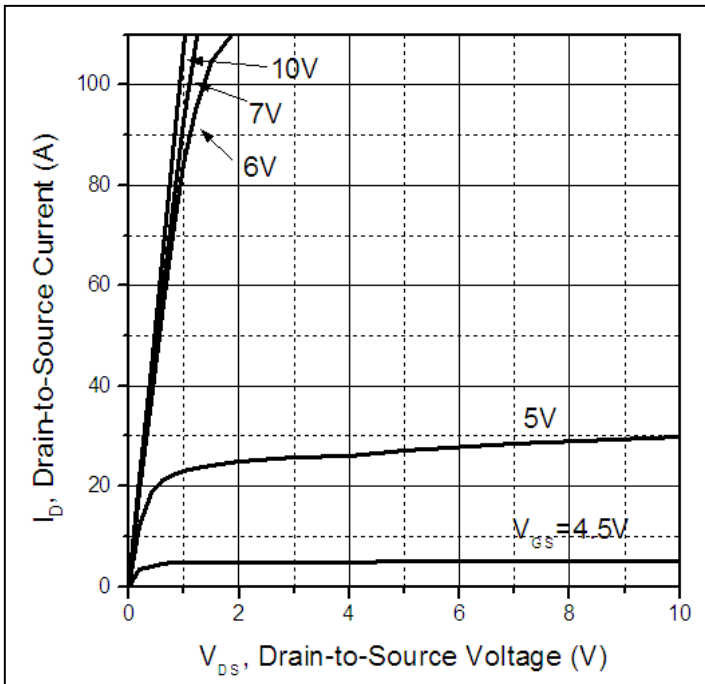
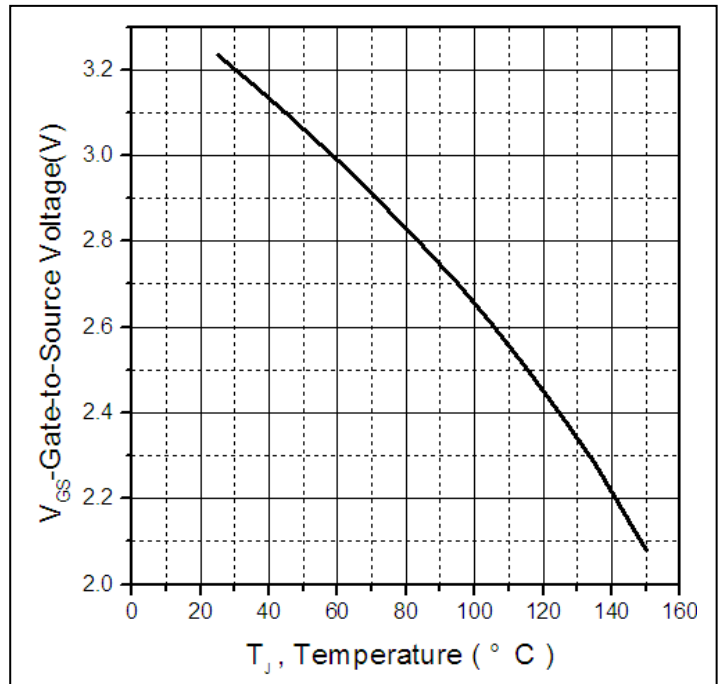
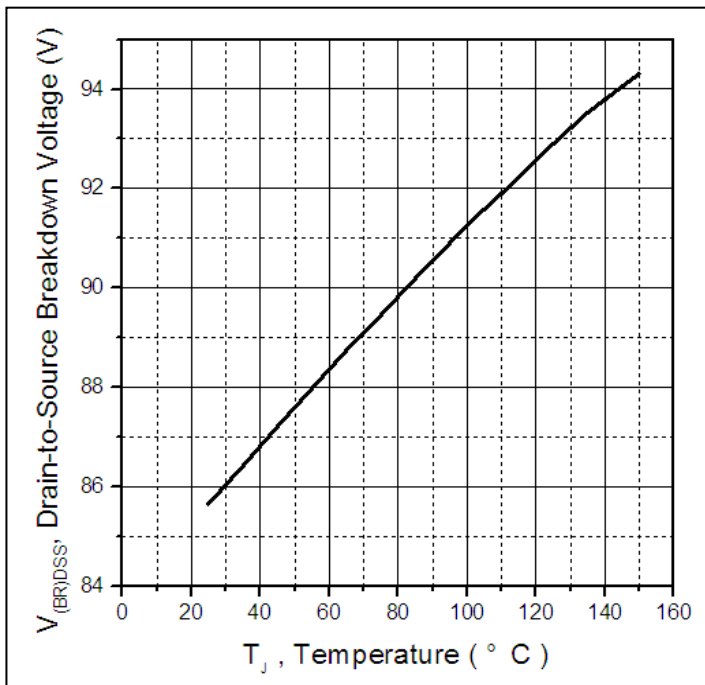
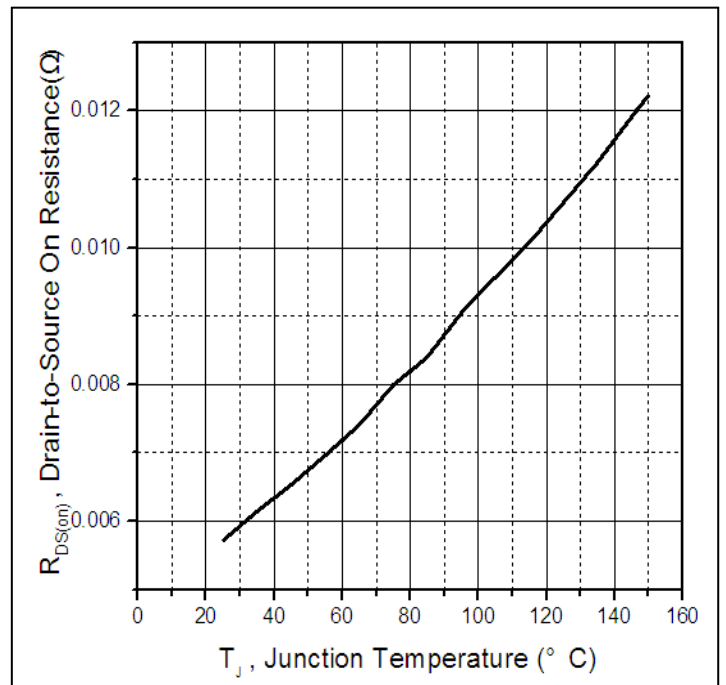
| Symbol | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---------------|--------------------------------------|------|------|------|-------|--|
| $V_{(BR)DSS}$ | Drain-to-Source breakdown voltage | 75 | — | — | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| $R_{DS(on)}$ | Static Drain-to-Source on-resistance | — | 6 | 8 | mΩ | $V_{GS}=10V, I_D = 30A$ $T_J = 125^\circ\text{C}$ |
| | | — | 10.5 | — | | |
| $V_{GS(th)}$ | Gate threshold voltage | 2 | — | 4 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ $T_J = 125^\circ\text{C}$ |
| | | — | 2.4 | — | | |
| I_{DSS} | Drain-to-Source leakage current | — | — | 1 | μA | $V_{DS} = 75V, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$ |
| | | — | — | 50 | | |
| I_{GSS} | Gate-to-Source forward leakage | — | — | 100 | nA | $V_{GS} = 20V$ $V_{GS} = -20V$ |
| | | — | — | -100 | | |
| Q_g | Total gate charge | — | 118 | — | nC | $I_D = 30A,$ $V_{DS}=30V,$ $V_{GS} = 10V$ |
| Q_{gs} | Gate-to-Source charge | — | 25 | — | | |
| Q_{gd} | Gate-to-Drain("Miller") charge | — | 43 | — | | |
| $t_{d(on)}$ | Turn-on delay time | — | 20 | — | ns | $V_{GS}=10V, V_{DS}=30V,$ $R_L=15\Omega,$ $R_{GEN}=2.55\Omega$ |
| t_r | Rise time | — | 18 | — | | |
| $t_{d(off)}$ | Turn-Off delay time | — | 67 | — | | |
| t_f | Fall time | — | 26 | — | | |
| C_{iss} | Input capacitance | — | 4972 | — | pF | $V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 800\text{KHz}$ |
| C_{oss} | Output capacitance | — | 402 | — | | |
| C_{rss} | Reverse transfer capacitance | — | 366 | — | | |

Source-Drain Ratings and Characteristics

| Symbol | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------|---|------|------|------|-------|--|
| I_S | Continuous Source Current (Body Diode) | — | — | 100 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I_{SM} | Pulsed Source Current (Body Diode) | — | — | 400 | A | |
| V_{SD} | Diode Forward Voltage | — | 0.88 | 1.3 | V | $I_S=30A, V_{GS}=0V$ |
| t_{rr} | Reverse Recovery Time | — | 45.7 | — | ns | $T_J = 25^\circ\text{C}, I_F = 75A,$ |
| Q_{rr} | Reverse Recovery Charge | — | 91 | — | nC | $di/dt = 100A/\mu s$ |

Test circuits and Waveforms
EAS test circuits:

Gate charge test circuit:

Switch Time Test Circuit:

Switch Waveforms:

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$

Typical electrical and thermal characteristics

Figure 1: Typical Output Characteristics

Figure 2. Gate to source cut-off voltage

Figure 3. Drain-to-Source Breakdown Voltage vs. Temperature

Figure 4: Normalized On-Resistance Vs. Case Temperature

Typical electrical and thermal characteristics

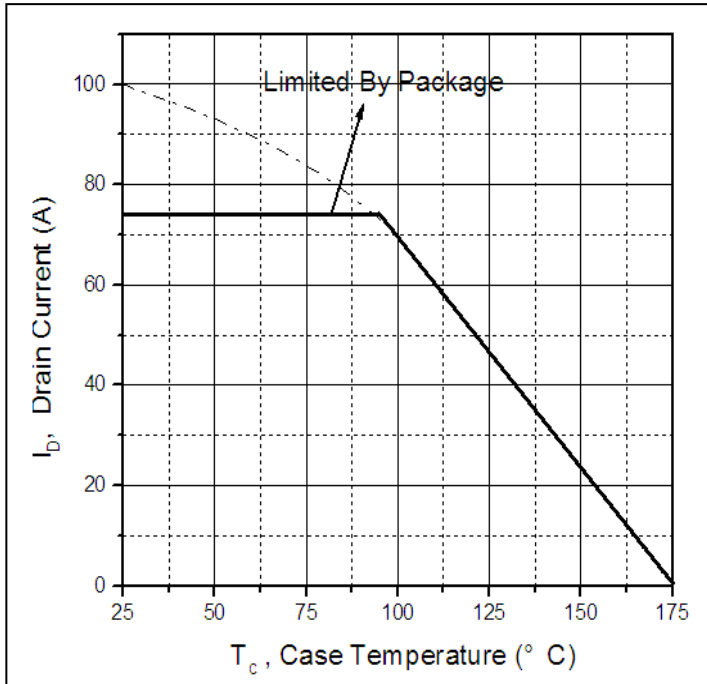


Figure 5. Maximum Drain Current Vs. Case Temperature

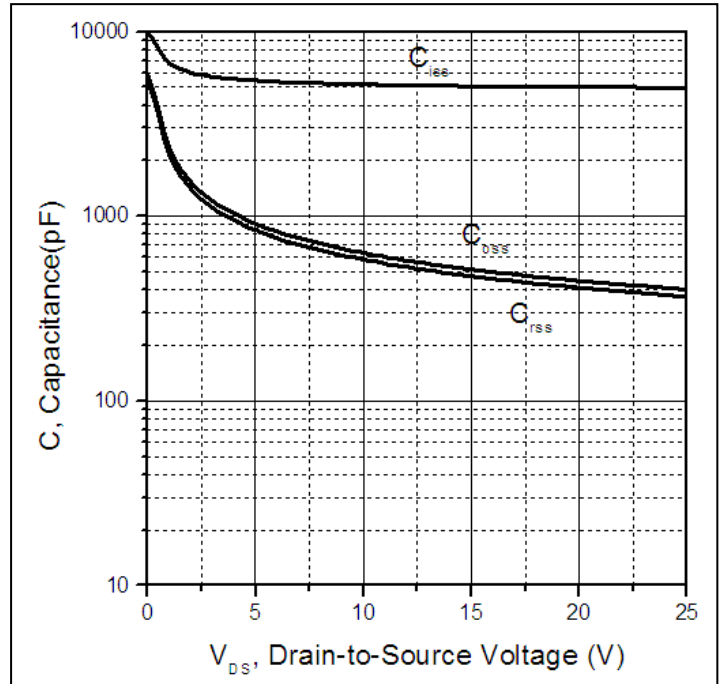


Figure 6. Typical Capacitance Vs. Drain-to-Source Voltage

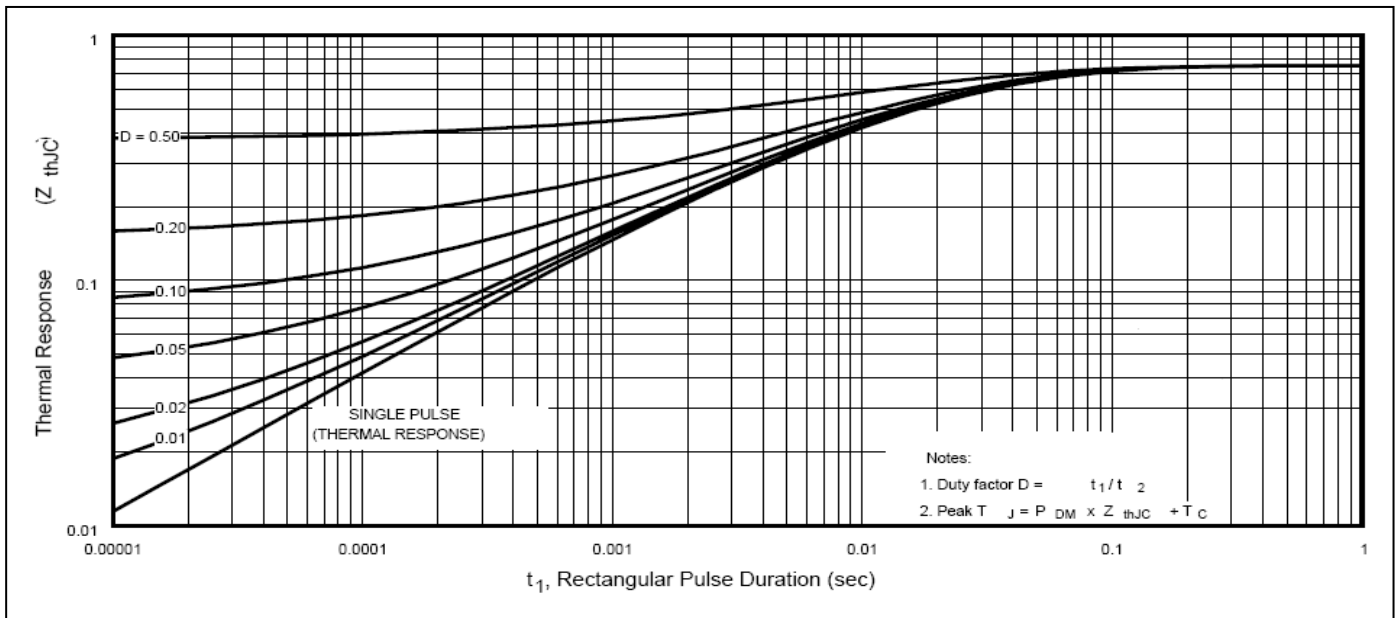
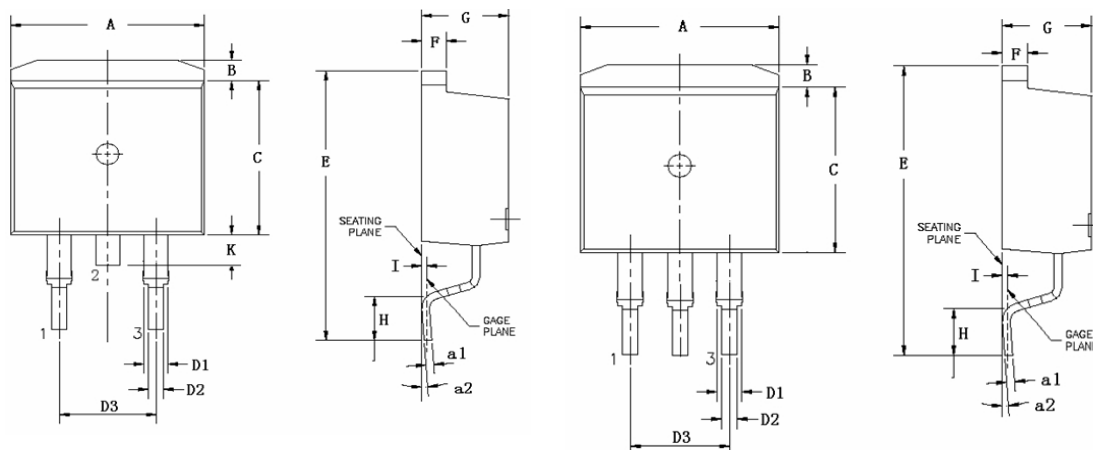


Figure 7. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Mechanical Data:
TO263 PACKAGE OUTLINE DIMENSION


| Symbol | Dimension In Millimeters | | Dimension In Inches | |
|--------|--------------------------|----------------|---------------------|----------------|
| | Min | Max | Min | Max |
| A | 9.660 | 10.280 | 0.380 | 0.405 |
| B | 1.020 | 1.320 | 0.040 | 0.052 |
| C | 8.590 | 9.400 | 0.338 | 0.370 |
| D1 | 1.140 | 1.400 | 0.045 | 0.055 |
| D2 | 0.700 | 0.950 | 0.028 | 0.037 |
| D3 | 5.080 (TYP) | | 0.200 (TYP) | |
| E | 15.090 | 15.390 | 0.594 | 0.606 |
| F | 1.150 | 1.400 | 0.045 | 0.055 |
| G | 4.300 | 4.700 | 0.169 | 0.185 |
| H | 2.290 | 2.790 | 0.090 | 0.110 |
| I | 0.250 (TYP) | | 0.010 (TYP) | |
| K | 1.300 | 1.600 | 0.051 | 0.063 |
| a1 | 0.450 | 0.650 | 0.018 | 0.026 |
| a2 | 0 ⁰ | 8 ⁰ | 1 ⁰ | 8 ⁰ |

Ordering and Marking Information**Device Marking: SSF7508A****Package (Available)****D2PAK(TO263)****Operating Temperature Range****C : -55 to 175 °C****Devices per Unit**

| Package Type | Units/Tube | Tubes/Inner Box | Units/Inner Box | Inner Boxes/ Carton Box | Units/ Carton Box |
|---------------------|-------------------|------------------------|------------------------|--------------------------------|--------------------------|
| D2PAK | 50 | 20 | 1000 | 6 | 6000 |

Reliability Test Program

| Test Item | Conditions | Duration | Sample Size |
|--|--|---|----------------------------|
| High Temperature Reverse Bias(HTRB) | T_j=125°C to 175°C @ 80% of Max V_{DSS}/V_{CES}/V_R | 168 hours 500 hours 1000 hours | 3 lots x 77 devices |
| High Temperature Gate Bias(HTGB) | T_j=150°C or 175°C @ 100% of Max V_{GSS} | 168 hours 500 hours 1000 hours | 3 lots x 77 devices |

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